

Low Power Precision Operational Amplifier

PM1012

FEATURES

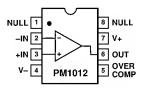
Low Supply Current: 600 μA Max Very Low Offset: 35 μV Max Low Drift: 1.5 μV/°C Max Very Low Bias Current 25°C: 100 pA Max

Low Noise: 0.5 μV p-p Typ

High Common-Mode Rejection: 114 dB Min

PIN CONNECTIONS

Plastic Mini-DIP (P Suffix) 8-Lead SO (S Suffix)



GENERAL DESCRIPTION

The PM 1012 is a general purpose, precision operational amplifier. Offering several performance enhancements over industry-standard precision op amps such as the OP07, the PM 1012 requires less than 1/6 the supply current. These enhancements include exceptionally low bias currents of only $\pm 80~\text{pA}$, typical, over the full military temperature range, and 132 dB of common-mode rejection and power-supply rejection. The PM 1012's low offset voltage of 35 μV maximum frees the user from external nulling in most circuits.

An open-loop gain of two million into a 10 k Ω load ensures that excellent linearity is maintained even in high gain configurations, and 5 mA of output current allows 2 k Ω loads to be driven with an open-loop gain of one million. The PM 1012 offers low noise, especially for a low power amplifier—only $17 \text{ nV}/\overline{\text{Hz}}$ at 10 Hz. Exceptionally low current noise minimizes

noise contributions when high source impedances are used. The PM 1012 may be overcompensated, using Pin 5 to limit the amplifier's bandwidth, further reducing system noise and increasing stability with large capacitive loads.

The PM 1012 conforms to the OP07 pinout with nulling through Pins 1 and 8 to the positive supply. It offers an upgrade to the OP07 in sockets where reduced power dissipation or low bias currents are attractive. It may also be used as an upgrade from the OP12, OP05 and 725 type op amps. The PM 1012 may replace 741 type op amps by removing the nulling potentiometer, if used.

PM1012- SPECIFICATIONS

ELECTRICAL CHARACTERISTICS (@ $V_S = \pm 15 \text{ V}$, $V_{CM} = 0 \text{ V}$, $T_A = +25 ^{\circ}\text{C}$, unless otherwise noted)

				PM 1012G		
Parameter	Symbol	Conditions	Min	Тур	Max	Units
Input Offset Voltage	Vos	(N ote 1)		10 25	50 120	μV μV
L ong-T erm V _{os} Stability Input Offset Current	ΔV _{os} /T ime	(N ote 1)		0.3 20	150	μV/M onth pA
Input Bias Current	I _B	(N ote 1)		30 ±30 ±40	200 ±150 ±200	pA pA pA
Input Noise Voltage Input Noise Voltage Density	e _n p-p e _n	0.1 Hz to 10 Hz $f_0 = 10 \text{ Hz}^2$ $f_0 = 1000 \text{ Hz}^3$		0.5 17 14	30 22	μV p-p nV/√Hz nV/√Hz
Input Noise Current Density Large-Signal Voltage Gain	I _n A _{VO}	$f_{O} = 10 \text{ Hz}$ $V_{O} = \pm 12 \text{ V}; R_{L} = 10 \text{ k}\Omega$ $V_{O} = \pm 10 \text{ V}; R_{L} = 2 \text{ k}\Omega$	200 120	20 2000 1000		fA/√Hz V/mV V/mV
C ommon-M ode Rejection Power-Supply Rejection Input Voltage Range	CMR PSR IVR	$V_{CM} = \pm 13.5 \text{ V}$ $V_{S} = \pm 2 \text{ V to } \pm 20 \text{ V}$ (N ote 4)	110 110 ±13.5	132 132 ±14.0		dB dB V
Output Voltage Swing Slew Rate	V _o SR	$R_L = 10 \text{ k}\Omega$	±13.5 ±13 0.1	±14 0.2		V V/μs
Full-Power Bandwidth Gain Bandwidth Product Supply Current	BW _P GBW I _{SY}	A _V = +100 (N ote 1)		3 0.5 380	600	kHz MHz μA
Supply Voltage	Vs	Operating Range	±2	±15	± 20	v

NOTES

ELECTRICAL CHARACTERISTICS (@ $V_S = \pm 15 \text{ V}$, $V_{CM} = 0 \text{ V}$, $-40^{\circ}\text{C} \le T_A \le +85^{\circ}\text{C}$ for PM1012GP, GS, unless otherwise noted)

				PM 1012G		
Parameter	Symbol	Conditions	Min	Тур	Max	Units
Input Offset Voltage	Vos			20 30	120 200	μV μV
A verage T emperature C oefficient of V _{OS}	TCVos	(N ote 1)		0.2	1.5	μV/°C
Input Offset Current	los	(N ote 1)		20 40	230 300	pA pA
Average T emperature Coefficient of I _{OS}	TClos			0.3	2.5	pA/°C
Input Bias Current	I _B	(Note 1)		±35 ±50	±230 ±300	pA pA pA
A verage T emperature				_ 5 0	_500	
Coefficient of I _B	TCIB			0.3	2.5	pA/°C
L arge Signal Voltage G ain	A _{VO}	$V_0 = \pm 12 \text{ V}; R_L = 10 \text{ k}\Omega$	150	1500		V/mV
		$V_0 = \pm 10 \text{ V}; R_L = 2 \text{ k}\Omega$	100	800		V/mV
Common-Mode Rejection	CMR	$V_{CM} = \pm 13.5 \text{ V}$	108	130		dB
Power Supply Rejection	PSR	$V_{S} = \pm 2.5 \text{ V to } \pm 20 \text{ V}$	108	128		dB
Input Voltage Range	IVR	(N ote 2)	±13.5	± 14.0		V
Output Voltage Swing	Vo	$R_L = 10 \text{ k}\Omega$	±13	± 14		V
Slew Rate	SR		0.05	0.15		V/μs
Supply Current	I _{SY}	(N ote 1)		400	800	μA
Supply Voltage	Vs	O perating Range	±2.5	±15	± 20	V

NOTES

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 $^{^{1}}$ T hese specifications apply for ± 2 V \leq V $_{S}$ \leq ± 20 V and -13.5 V \leq V $_{CM}$ \leq +13.5 V (for V $_{S}$ = ± 15 V). 2 10 H z noise voltage density is sample tested. D evices 100% tested for noise are available on request.

³Sample tested.

⁴Guaranteed by CMR test.

Specifications subject to change without notice.

 $^{^{1}}$ T hese specifications apply for ± 2.5 V \leq V $_{S}$ \leq ± 20 V and -13.5 V \leq V $_{CM}$ \leq +13.5 V (for V $_{S}$ = ± 15 V).

²Guaranteed by CMR test.

Specifications subject to change without notice.

PM1012

ABSOLUTE MAXIMUM RATINGS¹

Supply Voltage
Input Voltage ² ±20 V
Differential Input Voltage ³ ±1 V
Differential Input Current ³ ±10 mA
Output Short-Circuit Duration Indefinite
O perating T emperature R ange
PM 1012G (P, S)40°C to +85°C
Storage T emperature Range65°C to +150°C
Junction Temperature Range65°C to +150°C
Lead Temperature (Soldering, 60 sec) +300°C

Package Type	θ_{JA}^{4}	θ _{JC}	Units
8-Lead Plastic DIP (P)	103	43	°C/W
8-L ead SO (S)	158	43	°C/W

NOTES

 $^1\!A$ bsolute maximum ratings apply to both DICE and packaged parts, unless otherwise noted.

 2F or supply voltages less than $\pm 20~\text{V}$, the absolute maximum input voltage is equal to the supply voltage.

³The PM 1012's inputs are protected by back-to-back diodes. Current-limiting resistors are not used in order to achieve low noise. Differential input voltages greater than 1 V will cause excessive current to flow through the input protection diodes unless limiting resistance is used.

 $^4\theta_{JA}$ is specified for worst case mounting conditions, i.e., θ_{JA} is specified for device in socket for cerdip, and P-DIP packages; θ_{JA} is specified for device soldered to printed circuit board for SO package.

ORDERING GUIDE

Model	Temperature	Package	Package	
	Range	Description	Options	
PM 1012G P	-40°C to +85°C	Plastic DIP	N -8	
PM 1012G S	-40°C to +85°C	SOIC	SO-8	

CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the PM 1012 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.

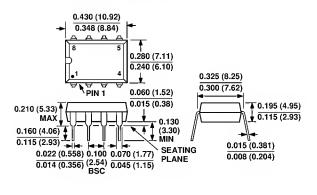


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OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

8-Lead Plastic DIP (N-8)



8-Lead SOIC (SO-8)

